JA07001000P50; 700 MHz – 1000 MHz 100W AMPLIFIER

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Small Dimensions & Light Weight
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Fast Switching Capability

ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

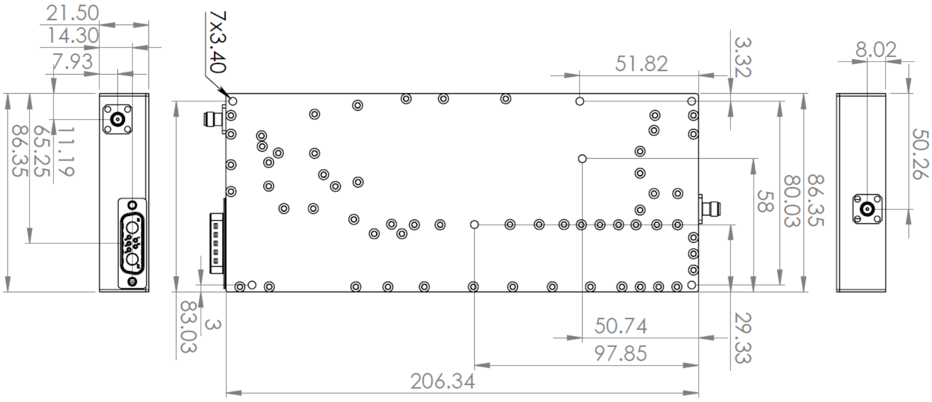
Frequency:	700-1000 MHz
Output Power:	100 W min. CW
Nominal Gain:	50 dB
Gain Flatness:	± 2 dB
Input VSWR:	2:1 max.
Load VSWR for Survival:	∞:1 for 1min.
DC Supply Voltage:	32 V
DC Current:	10 A Avg
Operating Case Temp.:	-40 ºC to 85 ºC
Storage Temperature:	-40 ºC to 85 ºC
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
7W2 DSUB:	A1) GND A2) 32 V 1) Temp. 2) Current 3) Rev. Power 4) Fwd. Power 5) Enable

MECHANICAL SPECIFICATIONS

Size (mm) :	206.3 x 86.4 x 21.5
Weight :	800 gr.
Plating :	Yellow Chromate



www.rftrelectronics.com sales@rftrelectronics.com

SPECIFICATIONS ARE SUBJECT TO CHANGE